

L Number	Hits	Search Text	DB	Time stamp
-	243718	((conductive conductor conducting metal) near5 (layer film)	USPAT; US-PGPUB	2002/08/29 09:46
-	163317	((dielectric insulating insulator) near5 (layer film)	USPAT; US-PGPUB	2002/08/29 09:31
-	106774	((conductive conductor conducting metal) near5 (layer film) ) and ((dielectric insulating insulator) near5 (layer film))	USPAT; US-PGPUB	2002/08/29 09:31
-	1261821	Sr Ba Pb Zr Bi Ta Ti Mg Nb barium strontium lead zirconium bismuth tantalum titanium magnesium niobium	USPAT; US-PGPUB	2002/08/29 09:50
-	70474	((conductive conductor conducting metal) near5 (layer film) ) and ((dielectric insulating insulator) near5 (layer film)) and (Sr Ba Pb Zr Bi Ta Ti Mg Nb barium strontium lead zirconium bismuth tantalum titanium magnesium niobium)	USPAT; US-PGPUB	2002/08/29 09:38
-	450	((((conductive conductor conducting metal) near5 (layer film) ) and ((dielectric insulating insulator) near5 (layer film))) and (Sr Ba Pb Zr Bi Ta Ti Mg Nb barium strontium lead zirconium bismuth tantalum titanium magnesium niobium)) and polyimide	USPAT; US-PGPUB	2002/08/29 09:38
-	18810	((((conductive conductor conducting metal) near5 (layer film) ) and ((dielectric insulating insulator) near5 (layer film))) and (Sr Ba Pb Zr Bi Ta Ti Mg Nb barium strontium lead zirconium bismuth tantalum titanium magnesium niobium)) and capacitor	USPAT; US-PGPUB	2002/08/29 09:38
-	0	(((((conductive conductor conducting metal) near5 (layer film) ) and ((dielectric insulating insulator) near5 (layer film))) and (Sr Ba Pb Zr Bi Ta Ti Mg Nb barium strontium lead zirconium bismuth tantalum titanium magnesium niobium)) and capacitor) and olymide	USPAT; US-PGPUB	2002/08/29 09:39
-	117	(((((conductive conductor conducting metal) near5 (layer film) ) and ((dielectric insulating insulator) near5 (layer film))) and (Sr Ba Pb Zr Bi Ta Ti Mg Nb barium strontium lead zirconium bismuth tantalum titanium magnesium niobium)) and capacitor) and polyimide	USPAT; US-PGPUB	2002/08/29 09:40
-	36846	capacitor and ((conductive conductor conducting metal) near5 (layer film)) and ((dielectric insulating insulator) near5 (film layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 09:49
-	13310	((capacitor and ((conductive conductor conducting metal) near5 (layer film)) and ((dielectric insulating insulator) near5 (film layer))) and (Sr Ba Pb Zr Bi Ta Ti Mg Nb barium strontium zirconium bismuth tantalum titanium magnesium niobium)	USPAT; US-PGPUB	2002/08/29 10:16
-	82	((capacitor and ((conductive conductor conducting metal) near5 (layer film)) and ((dielectric insulating insulator) near5 (film layer))) and (Sr Ba Pb Zr Bi Ta Ti Mg Nb barium strontium zirconium bismuth tantalum titanium magnesium niobium)) and polyimide	USPAT; US-PGPUB	2002/10/11 08:30
-	87	((capacitor and ((conductive conductor conducting metal) near5 (layer film)) and ((dielectric insulating insulator) near5 (film layer))) and (Sr Ba Pb Zr Bi Ta Ti Mg Nb barium strontium zirconium bismuth tantalum titanium magnesium niobium)) and polyimide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 08:32

L Number	Hits	Search Text	DB	Time stamp
-	429	257/528	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:30
-	1778	257/532	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:30
-	343	257/534	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:30
-	242	257/535	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:30
-	2331	257/774	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:30
-	1737	257/738	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:30
-	2149	257/737	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:30
-	2020	257/700	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:31
-	1503	257/701	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:31
-	3120	257/758	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:31
-	591	257/759	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:31
-	886	257/760	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:31
-	1019	257/288	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:31
-	223	257/395	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:31
-	1024	257/310	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:31
-	3236	257/296	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:31
-	905	257/303	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:31

-	190	257/516	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:31
-	178	257/595	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:31
-	78	257/602	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:32
-	17419	257/528 257/532 257/534 257/535 257/774 257/738 257/737 257/700 257/701 257/758 257/759 257/760 257/288 257/395 257/310 257/296 257/303 257/516 257/595 257/602	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 15:50
-	6350	(257/528 257/532 257/534 257/535 257/774 257/738 257/737 257/700 257/701 257/758 257/759 257/760 257/288 257/395 257/310 257/296 257/303 257/516 257/595 257/602) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:34
-	4740	((257/528 257/532 257/534 257/535 257/774 257/738 257/737 257/700 257/701 257/758 257/759 257/760 257/288 257/395 257/310 257/296 257/303 257/516 257/595 257/602) and capacitor) and (metal conducting conductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:35
-	4330	((((257/528 257/532 257/534 257/535 257/774 257/738 257/737 257/700 257/701 257/758 257/759 257/760 257/288 257/395 257/310 257/296 257/303 257/516 257/595 257/602) and capacitor) and (metal conducting conductor)) and (dielectric insulator insulating)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:35
-	3035	(((((257/528 257/532 257/534 257/535 257/774 257/738 257/737 257/700 257/701 257/758 257/759 257/760 257/288 257/395 257/310 257/296 257/303 257/516 257/595 257/602) and capacitor) and (metal conducting conductor)) and (dielectric insulator insulating)) and (Sr Ba Pb Zr Bi Ta Ti Mg Nb bismuth magnesium lead barium strontium zirconium tantalum titanium niobium)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 14:36
-	2514	(((((257/528 257/532 257/534 257/535 257/774 257/738 257/737 257/700 257/701 257/758 257/759 257/760 257/288 257/395 257/310 257/296 257/303 257/516 257/595 257/602) and capacitor) and (metal conducting conductor)) and (dielectric insulator insulating)) and (Sr Ba Pb Zr Bi Ta Ti Mg Nb bismuth magnesium lead barium strontium zirconium tantalum titanium niobium)) and oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 13:45
-	1557	(((((257/528 257/532 257/534 257/535 257/774 257/738 257/737 257/700 257/701 257/758 257/759 257/760 257/288 257/395 257/310 257/296 257/303 257/516 257/595 257/602) and capacitor) and (metal conducting conductor)) and (dielectric insulator insulating)) and (Sr Ba Pb Zr Bi Ta Ti Mg Nb bismuth magnesium lead barium strontium zirconium tantalum titanium niobium)) and oxide) and (Pt Au Cu Pd Ru Ir platinum gold copper palladium ruthenium iridium)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 14:41

-	110	(((((257/528 257/532 257/534 257/535 257/774 257/738 257/737 257/700 257/701 257/758 257/759 257/760 257/288 257/395 257/310 257/296 257/303 257/516 257/595 257/602) and capacitor) and (metal conducting conductor)) and (dielectric insulator insulating)) and (Sr Ba Pb Zr Bi Ta Ti Mg Nb bismuth magnesium lead barium strontium zirconium tantalum titanium niobium)) and oxide) and (Pt Au Cu Pd Ru Ir platinum gold copper palladium ruthenium iridium)) and (silicon near dioxide)) and (polymide polyimide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 10:42
-	582	(((((257/528 257/532 257/534 257/535 257/774 257/738 257/737 257/700 257/701 257/758 257/759 257/760 257/288 257/395 257/310 257/296 257/303 257/516 257/595 257/602) and capacitor) and (metal conducting conductor)) and (dielectric insulator insulating)) and (Sr Ba Pb Zr Bi Ta Ti Mg Nb bismuth magnesium lead barium strontium zirconium tantalum titanium niobium)) and oxide) and (Pt Au Cu Pd Ru Ir platinum gold copper palladium ruthenium iridium)) and (silicon near dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 14:50
-	472	(((((257/528 257/532 257/534 257/535 257/774 257/738 257/737 257/700 257/701 257/758 257/759 257/760 257/288 257/395 257/310 257/296 257/303 257/516 257/595 257/602) and capacitor) and (metal conducting conductor)) and (dielectric insulator insulating)) and (Sr Ba Pb Zr Bi Ta Ti Mg Nb bismuth magnesium lead barium strontium zirconium tantalum titanium niobium)) and oxide) and (Pt Au Cu Pd Ru Ir platinum gold copper palladium ruthenium iridium)) and (silicon near dioxide)) not ((((((257/528 257/532 257/534 257/535 257/774 257/738 257/737 257/700 257/701 257/758 257/759 257/760 257/288 257/395 257/310 257/296 257/303 257/516 257/595 257/602) and capacitor) and (metal conducting conductor)) and (dielectric insulator insulating)) and (Sr Ba Pb Zr Bi Ta Ti Mg Nb bismuth magnesium lead barium strontium zirconium tantalum titanium niobium)) and oxide) and (Pt Au Cu Pd Ru Ir platinum gold copper palladium ruthenium iridium)) and (silicon near dioxide)) and (polymide polyimide))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 14:30
-	2577	capacitor near10 dielectric near10 thin near10 film	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 14:32
-	1510	(capacitor near10 dielectric near10 thin near10 film) and (Sr Ba Pb Zr Bi Ta Ti Mg Nb bismuth magnesium lead barium strontium zirconium tantalum titanium niobium)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 14:37
-	959	((capacitor near10 dielectric near10 thin near10 film) and (Sr Ba Pb Zr Bi Ta Ti Mg Nb bismuth magnesium lead barium strontium zirconium tantalum titanium niobium)) and (Pt Au Cu Pd Ru Ir platinum gold copper palladium ruthenium iridium)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 14:43
-	822	((capacitor near10 dielectric near10 thin near10 film) and (Sr Ba Pb Zr Bi Ta Ti Mg Nb bismuth magnesium lead barium strontium zirconium tantalum titanium niobium)) and (Pt Au Cu Pd Ru Ir platinum gold copper palladium ruthenium iridium)) and oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 14:43

-	114	(((((capacitor near10 dielectric near10 thin near10 film) and (Sr Ba Pb Zr Bi Ta Ti Mg Nb bismuth magnesium lead barium strontium zirconium tantalum titanium niobium)) and (Pt Au Cu Pd Ru Ir platinum gold copper palladium ruthenium iridium)) and oxide) and (polymide polyimide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 14:44
-	208	(((((capacitor near10 dielectric near10 thin near10 film) and (Sr Ba Pb Zr Bi Ta Ti Mg Nb bismuth magnesium lead barium strontium zirconium tantalum titanium niobium)) and (Pt Au Cu Pd Ru Ir platinum gold copper palladium ruthenium iridium)) and oxide) and (silicon near dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 14:50
-	177	(((((capacitor near10 dielectric near10 thin near10 film) and (Sr Ba Pb Zr Bi Ta Ti Mg Nb bismuth magnesium lead barium strontium zirconium tantalum titanium niobium)) and (Pt Au Cu Pd Ru Ir platinum gold copper palladium ruthenium iridium)) and oxide) and (silicon near dioxide)) not	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/10 14:51
-	4	(((((capacitor near10 dielectric near10 thin near10 film) and (Sr Ba Pb Zr Bi Ta Ti Mg Nb bismuth magnesium lead barium strontium zirconium tantalum titanium niobium)) and (Pt Au Cu Pd Ru Ir platinum gold copper palladium ruthenium iridium)) and oxide) and (polymide polyimide))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 08:58
-	10	"5882175"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 09:53
-	11	"6027947"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 09:15
-	3	"6225185"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 09:45
-	1114	NSG	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 09:50
-	135183	Sr "Bi.sub.2" "Ta.sub.2" "O.sub.9"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 09:55
-	427	"SrBi.sub.2" adj "Ta.sub.2" adj "O.sub.9"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 10:27
-	394	("SrBi.sub.2" adj "Ta.sub.2" adj "O.sub.9") and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 09:57
-	136619	((Ba,Sr) adj "TiO.sub.3") (Pb(Zr,Ti)adj "O.sub.3") ("Ta.sub.2" adj "O.sub.5") (Pb(Mg,Nb) adj "O.sub.3")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 10:04
-	136738	("SrBi.sub.2" adj "Ta.sub.2" adj "O.sub.9") ((Ba,Sr) adj "TiO.sub.3") (Pb(Zr,Ti)adj "O.sub.3") ("Ta.sub.2" adj "O.sub.5") (Pb(Mg,Nb) adj "O.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 10:04

-	413	"(Ba,Sr)" adj "TiO.sub.3"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 10:22
-	487	Pb adj "(Zr,Ti)" adj "O.sub.3"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 10:24
-	41	Pb adj "(Mg,Nb)" adj "O.sub.3"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 10:25
-	6480	"Ta.sub.2" adj "O.sub.5"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 10:27
-	7278	"SrBi.sub.2" adj "Ta.sub.2" adj "O.sub.9") ("(Ba,Sr)" adj "TiO.sub.3") (Pb adj "(Zr,Ti)" adj "O.sub.3") (Pb adj "(Mg,Nb)" adj "O.sub.3") ("Ta.sub.2" adj "O.sub.5"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 10:28
-	2811	((("SrBi.sub.2" adj "Ta.sub.2" adj "O.sub.9") ("(Ba,Sr)" adj "TiO.sub.3") (Pb adj "(Zr,Ti)" adj "O.sub.3") (Pb adj "(Mg,Nb)" adj "O.sub.3") ("Ta.sub.2" adj "O.sub.5")) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 10:28
-	1159	((("SrBi.sub.2" adj "Ta.sub.2" adj "O.sub.9") ("(Ba,Sr)" adj "TiO.sub.3") (Pb adj "(Zr,Ti)" adj "O.sub.3") (Pb adj "(Mg,Nb)" adj "O.sub.3") ("Ta.sub.2" adj "O.sub.5")) and capacitor) and (conductor conductive conducting) and (insulator insulating insulation) and (dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 10:34
-	2112	((("SrBi.sub.2" adj "Ta.sub.2" adj "O.sub.9") ("(Ba,Sr)" adj "TiO.sub.3") (Pb adj "(Zr,Ti)" adj "O.sub.3") (Pb adj "(Mg,Nb)" adj "O.sub.3") ("Ta.sub.2" adj "O.sub.5")) near10 (insulator insulating insulation dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 10:36
-	1468	((("SrBi.sub.2" adj "Ta.sub.2" adj "O.sub.9") ("(Ba,Sr)" adj "TiO.sub.3") (Pb adj "(Zr,Ti)" adj "O.sub.3") (Pb adj "(Mg,Nb)" adj "O.sub.3") ("Ta.sub.2" adj "O.sub.5")) near10 (insulator insulating insulation dielectric)) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 10:39
-	311867	(metal conducting conductor conducting) near10 (Pt Au Cu Pd Ru Ir platinum gold copper palladium ruthenium iridium)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 10:45
-	558	((("SrBi.sub.2" adj "Ta.sub.2" adj "O.sub.9") ("(Ba,Sr)" adj "TiO.sub.3") (Pb adj "(Zr,Ti)" adj "O.sub.3") (Pb adj "(Mg,Nb)" adj "O.sub.3") ("Ta.sub.2" adj "O.sub.5")) near10 (insulator insulating insulation dielectric)) and capacitor) and (metal conducting conductor conducting) near10 (Pt Au Cu Pd Ru Ir platinum gold copper palladium ruthenium iridium)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 10:46
-	6350	(257/528 257/532 257/534 257/535 257/774 257/738 257/737 257/700 257/701 257/758 257/759 257/760 257/288 257/395 257/310 257/296 257/303 257/516 257/595 257/602) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 15:51
-	14082	(insulator insulation insulating) near10 (polyimide polyimide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/11 15:52

-	200	((257/528 257/532 257/534 257/535 257/774 257/738 257/737 257/700 257/701 257/758 257/759 257/760 257/288 257/395 257/310 257/296 257/303 257/516 257/595 257/602) and capacitor) and ((insulator insulation insulating) near10 (polymide polyimide))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/19 11:45
-	8	((("6180971") or ("5822175") or ("6225185") or ("5789303"))).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/19 11:45

L Number	Hits	Search Text	DB	Time stamp
1	1078345	semiconducto chip die flipchip (flip adj3 chip) (integrated adj circuit)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 13:27
2	6401	decoupling with (capacitor capacitance)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 13:26
3	1916287	semiconductor chip die flipchip (flip adj3 chip) (integrated adj circuit)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 13:27
4	3665	((decoupling with (capacitor capacitance)) and (semiconductor chip die flipchip (flip adj3 chip) (integrated adj circuit)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 13:28
5	2223	ground and power and ((decoupling with (capacitor capacitance)) and (semiconductor chip die flipchip (flip adj3 chip) (integrated adj circuit)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 13:28
6	798	(ground and power and ((decoupling with (capacitor capacitance)) and (semiconductor chip die flipchip (flip adj3 chip) (integrated adj circuit))) and pads	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 13:29
7	77451	(flexible bendable adjustable) with (substrate board)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 13:30
8	117	((ground and power and ((decoupling with (capacitor capacitance)) and (semiconductor chip die flipchip (flip adj3 chip) (integrated adj circuit))) and pads) and ((flexible bendable adjustable) with (substrate board)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 13:47
9	681	((ground and power and ((decoupling with (capacitor capacitance)) and (semiconductor chip die flipchip (flip adj3 chip) (integrated adj circuit))) and pads) not (((ground and power and ((decoupling with (capacitor capacitance)) and (semiconductor chip die flipchip (flip adj3 chip) (integrated adj circuit))) and pads) and ((flexible bendable adjustable) with (substrate board))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 13:48